



STPS30L30CT/CG/CR

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 15 A
V_{RRM}	30 V
$T_j (max)$	150 °C
$V_F (max)$	0.37 V

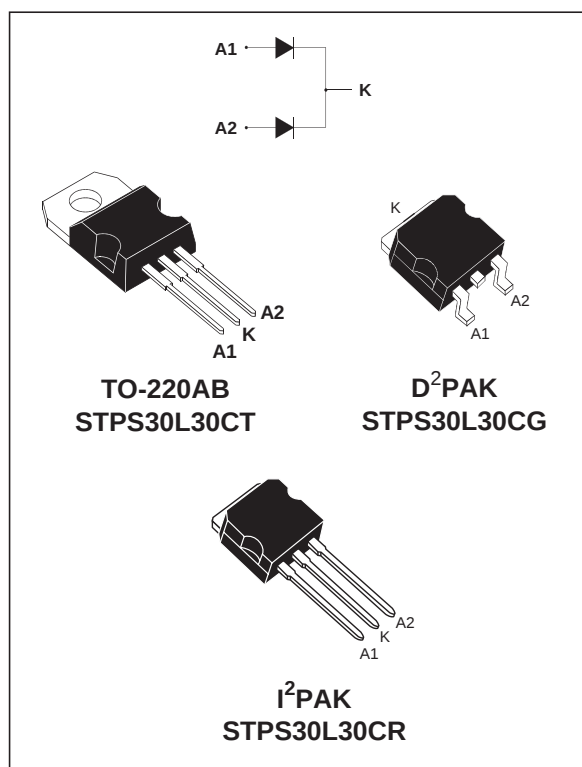
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, these devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			30	V
I _{F(RMS)}	RMS forward current			30	A
I _{F(AV)}	Average forward current	T _c = 140°C δ = 0.5	Per diode Per device	15 30	A
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal		220	A
I _{RRM}	Peak repetitive reverse current	tp = 2 μs F = 1kHz square		1	A
I _{RSM}	Non repetitive peak reverse current	tp = 100μs square		3	A
P _{ARM}	Repetitive peak avalanche power	tp = 1μs Tj = 25°C		5300	W
T _{stg}	Storage temperature range			- 65 to + 150	°C
Tj	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise reverse voltage			10000	V/μs

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THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode Total	1.5 0.8	°C/W
$R_{th(c)}$		Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			1.5	mA
		$T_j = 125^\circ\text{C}$			170	350	mA
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 15\text{ A}$			0.46	V
		$T_j = 125^\circ\text{C}$	$I_F = 15\text{ A}$		0.33	0.37	
		$T_j = 25^\circ\text{C}$	$I_F = 30\text{ A}$			0.57	
		$T_j = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.43	0.5	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.24 \times I_{F(AV)} + 0.009 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

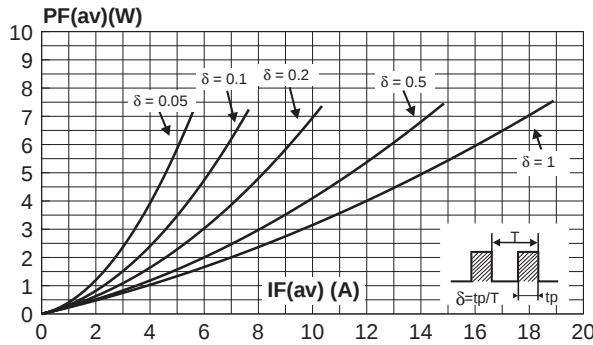


Fig. 3: Normalized avalanche power derating versus pulse duration.

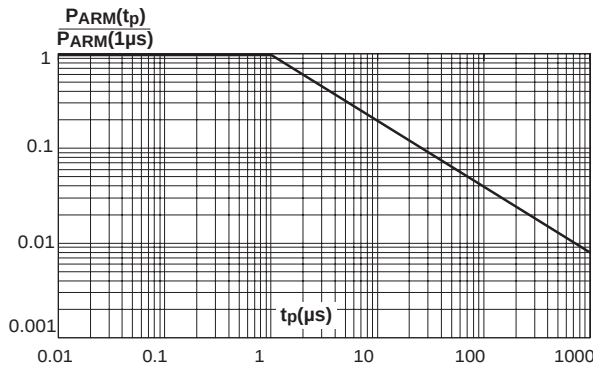


Fig. 2: Average current versus ambient temperature ($\delta=0.5$) (per diode).

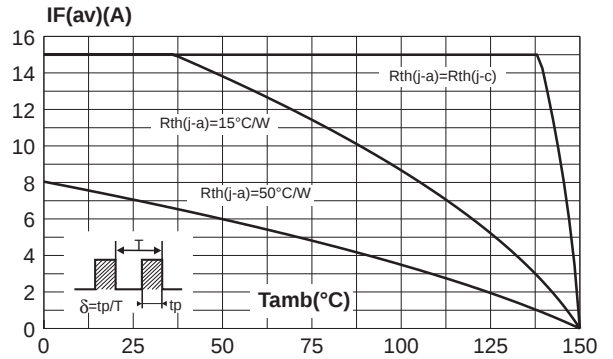


Fig. 4: Normalized avalanche power derating versus junction temperature.

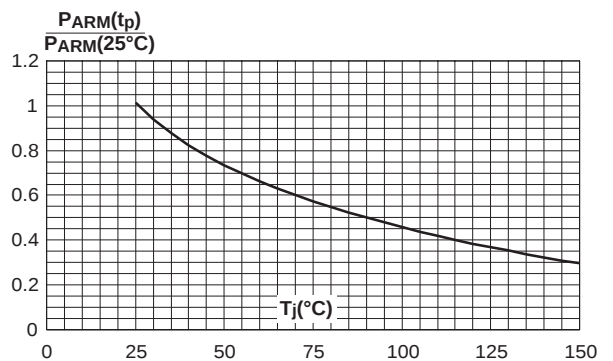


Fig. 4: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

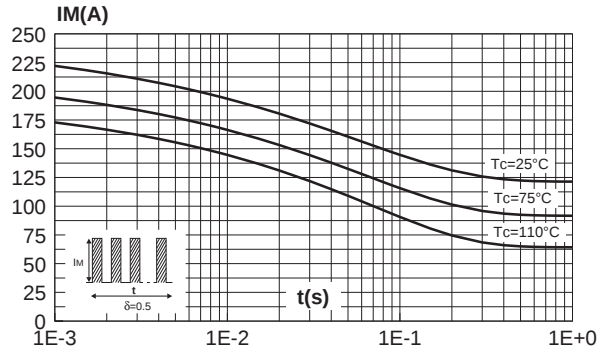


Fig. 5: Relative variation of thermal transient impedance junction to case versus pulse duration.

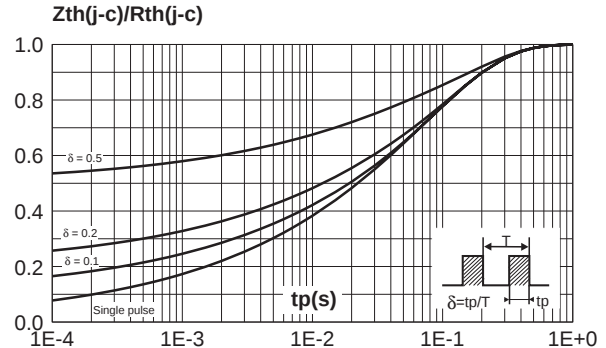


Fig. 6: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

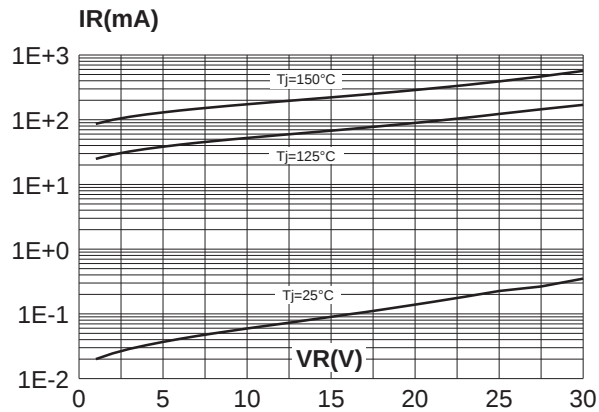


Fig. 7: Junction capacitance versus reverse voltage applied (typical values) (per diode).

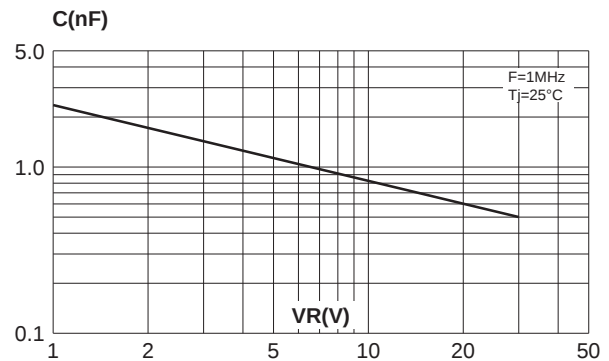


Fig. 8: Forward voltage drop versus forward current (maximum values - per diode).

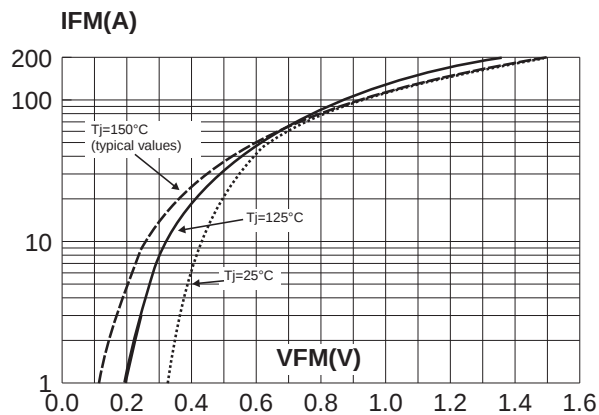
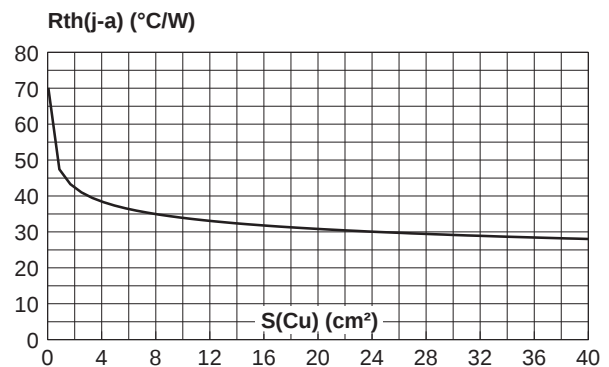
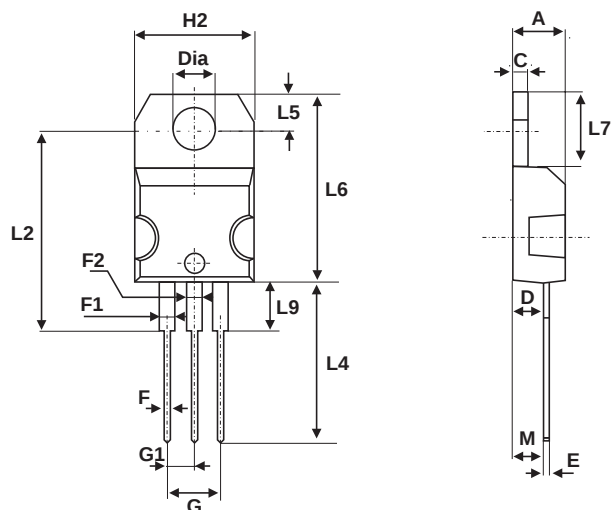


Fig. 9: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed circuit board FR4, $e(\text{Cu}) = 35\ \mu\text{m}$) (STPS30L30CG).



PACKAGE MECHANICAL DATA

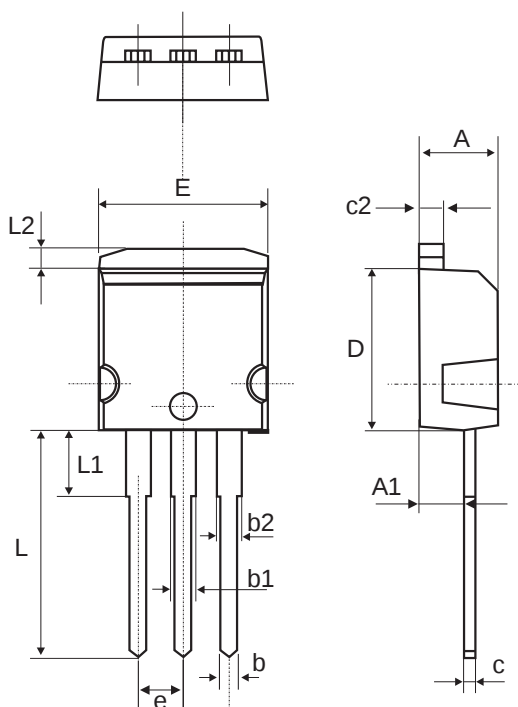
TO-220AB



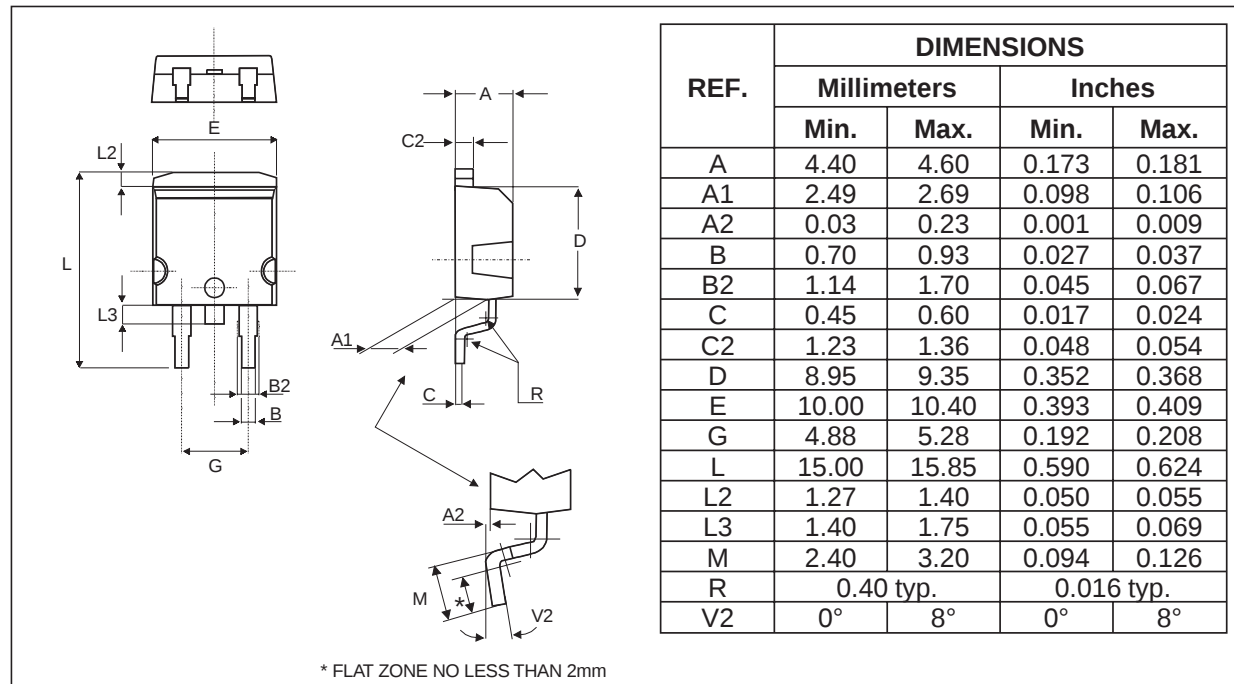
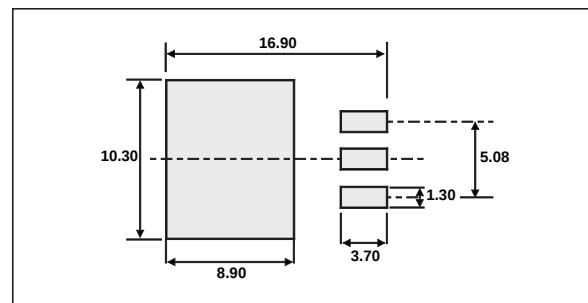
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

- Cooling method: C
- Recommended torque value: 0.55 m.N
- Maximum torque value: 0.70 m.N

PACKAGE MECHANICAL DATA



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
b	0.70	0.93	0.028	0.037
b1	1.14	1.17	0.044	0.046
b2	1.14	1.17	0.044	0.046
c	0.45	0.60	0.018	0.024
c2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
E	10.0	10.4	0.394	0.409
L	13.1	13.6	0.516	0.535
L1	3.48	3.78	0.137	0.149
L2	1.27	1.40	0.050	0.055

PACKAGE MECHANICAL DATA
D²PAK

FOOT PRINT (in millimeters)


Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS30L30CT	STPS30L30CT	TO-220AB	2g	50	Tube
STPS30L30CG	STPS30L30CG	D ² PAK	1.8g	50	Tube
STPS30L30CG-TR	STPS30L30CG	D ² PAK	1.8g	1000	Tape & reel
STPS30L30CR	STPS30L30CR	I ² PAK	1.49g	50	Tube

- Epoxy meets UL94,V0

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